



DOCKET NO. 99-039

RESPONSE UNDER 37 C.F.R. 1.116-
EXPEDITED PROCEDURE
EXAMINING GROUP 1765

#17/B
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9/30/02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: : Sheldon Aronowitz, Valeriy Sukharev, John Haywood, James P. Kimball,
Helmut Puchner, Ravindra Manohar Kapre, and Nicholas Eib

Appl. No. : 09/464,297


Filed: : December 15, 1999

Title : PROCESS FOR ETCHING A CONTROLLABLE THICKNESS OF
OXIDE ON AN INTEGRATED CIRCUIT STRUCTURE ON A
SEMICONDUCTOR SUBSTRATE USING NITROGEN PLASMA AND
AN RF BIAS APPLIED TO THE SUBSTRATE

Grp./ A.U. : 1765

Examiner : Charlotte A. Brown

Docket No. : 99-039

CERTIFICATE OF MAILING	
I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231	
o	September 20, 2002 (Date of Deposit)
John P. Taylor, Reg. No. 22,369	
 Signature	
September 20, 2002 Date of Signature	

AMENDMENT

Honorable Commissioner for Patents
Washington, D.C. 20231

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TC 1700

Date: September 20, 2002

Sir:

In response to the Final Rejection mailed July 31, 2002, please amend the application as follows: